



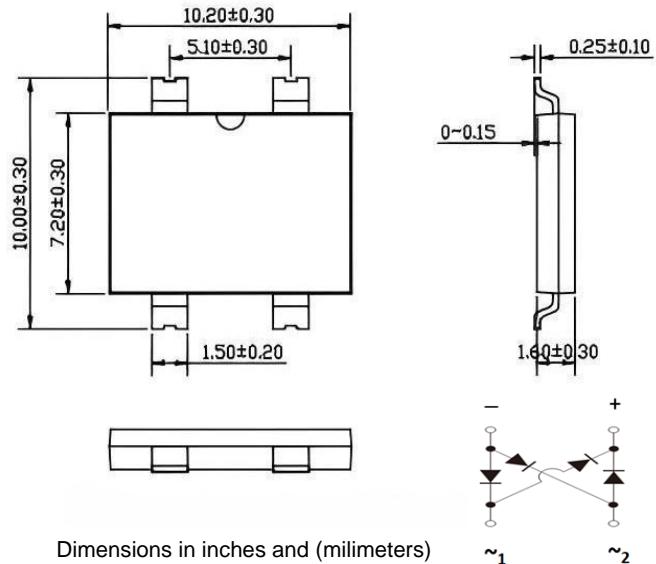
RHBS810

Glass Passivated Single-Phase 8.0Amp Surface Mount Bridge Rectifier

Features

- Surface mount bridge, small package;
- Ideal for printed circuit boards;
- Glass passivated chip junction;
- High forward current capability up to 8.0A;
- High surge current capability;
- High heat dissipation capability;
- Low profile package;
- Low forward voltage drop;
- Plastic package has Underwriters Laboratory Flammability Classification 94V-0;

Case: HBS



Dimensions in inches and (millimeters)

Mechanical Data

- Case: HBS;
Epoxy meets UL-94V-0 Flammability rating;
- Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD22-B102;
- High temperature soldering guaranteed:
Solder Reflow 260°C, 10seconds;
- Polarity: As marked on body;
- Marking: Type number;

Typical Applications

General purpose use in AC-to-DC bridge full wave rectification for Fast Charging, Switching Power Supply, USB PD, Adapter and 3-in-1 Power Board, etc.

Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified. Single Phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

Parameter	Symbol	RHBS810		Unit
Maximum repetitive peak reverse voltage	V_{RRM}	1000		V
Maximum RMS voltage	V_{RMS}	700		V
Maximum DC blocking voltage	V_{DC}	1000		V
Maximum average forward rectified output current at $T_A=25^\circ\text{C}$	$I_{F(AV)}$	8.0		Amps
Non-Repetitive Peak forward surge current 8.3 ms single sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	200		Amps
Rating for fusing ($t < 8.3\text{ms}$)	I^2t	166		A^2sec
Instantaneous forward voltage drop per diode @ $IF=1.0\text{A}$	V_F	0.95 max.		
Instantaneous forward voltage drop per diode @ $IF=4.0\text{A}$		1.1 max.		Volt
Instantaneous forward voltage drop per diode @ $IF=8.0\text{A}$		1.3max.		
Reverse Current at Rated DC Blocking Voltage $T_A=25^\circ\text{C}$	I_R	0.20 Typ.	5.0 max	μA
Reverse Current at Rated DC Blocking Voltage $T_A=125^\circ\text{C}$		50 Typ.	100 max.	
Maximum reverse recovery time ($IF=0.5\text{A}, IR=1.0\text{A}, Irr=0.25\text{A}$)	T_{rr}	350		nS
Typical thermal resistance	$R_{\Theta J-A}$ $R_{\Theta J-C}$ $R_{\Theta J-L}$	70.0 15.0 22.0		$^\circ\text{C/W}$
Operating junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150		$^\circ\text{C}$

Note1: Measured at 1.0MHz and applied reverse voltage of 5.0V DC;

Ratings and Characteristics Curves (TA = 25°C unless otherwise noted)

RHBS810

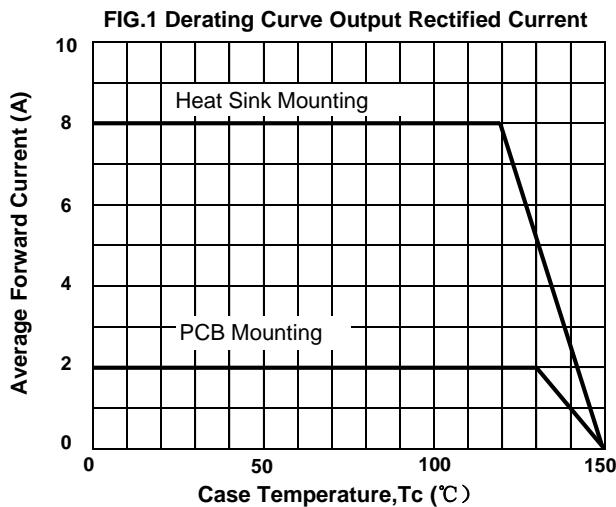


FIG.2 Typical Forward Characteristics per Diode

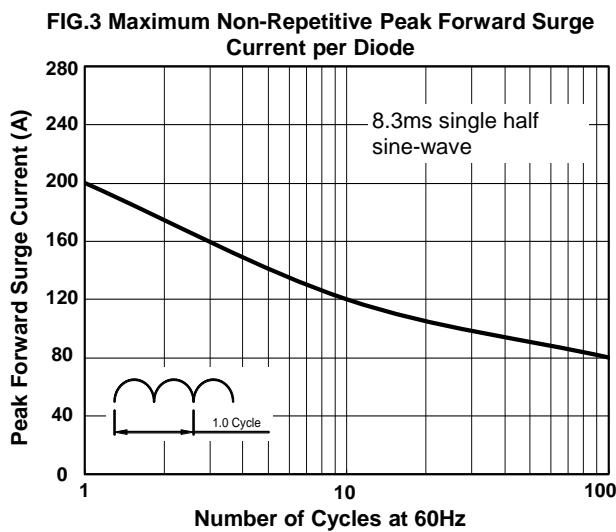
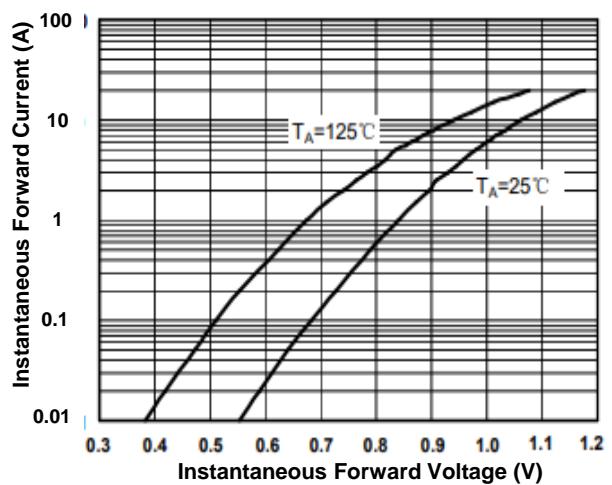
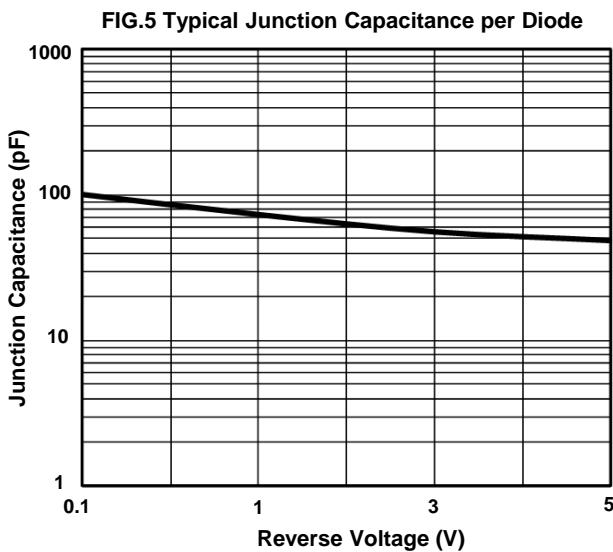
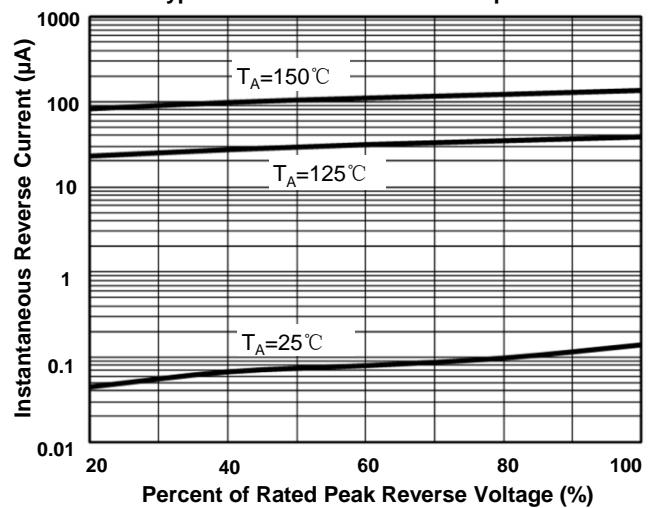


FIG.4 Typical Reverse Characteristics per Diode



Suggested PCB printfoot layout

Unit: inches (mm)

